

IN THE CLAIMS:

Amend claim 4 as follows:

4. (Amended) A method for manufacturing a semiconductor device, comprising:

forming a conductive portion on a substrate, wherein the conductive portion includes a gate electrode;

forming spacer on a side wall of the gate electrode;

depositing metal on the surface of the substrate including the conductive portion;

applying silicide on the conductive portion in a self-aligned manner by heat treating the substrate on which the metal is deposited;

removing residual metal that did not react during the heat treatment; and

repeating the depositing step, the silicide applying step, and the removing step once or a number of times.
